

REMARKS

Reconsideration and allowance are respectfully requested in light of the above amendments and the following remarks.

The Applicant respectfully submits that new Claims 20-23 are allowable for similar reasons as those set forth in the Amendment submitted December 12, 2002, regarding claims 1 and 18.

Moreover, claim 20 recites:

The method of claim 1, wherein:
the single crystalline substrate is formed from one of the group of Si, GaAs, ZnSe, SrTiO₃, and sapphire; and
the single crystalline film is formed from one of the group of Si, GaAs, Ga_{1-x}Al_xAs, ZnSe, ZnS, CdTe, ZnS_{1-x}Se_x, and YBCO.

And claim 21 recites:

The method of claim 1, wherein:
the single crystalline substrate is formed from one of the group of Si, GaAs, ZnSe, and SrTiO₃; and
the single crystalline film is formed from one of the group of Si, GaN, GaAs, Ga_{1-x}Al_xAs, ZnSe, ZnS, CdTe, ZnS_{1-x}Se_x, and YBCO.

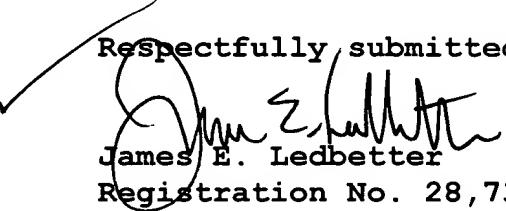
Tanaka, Tokunaga, and Nakamura fail to disclose the single crystalline substrate and film combinations recited in claims 20 and 21. Claims 22 and 23 recite similar combinations, but depend from claim 18. The particular combinations recited by claims 20-23 provide an independent basis for their allowability.

Therefore, it is submitted that allowance of claims 20-23 is warranted.

In view of the above, it is submitted that this application is in condition for allowance and a notice to that effect is respectfully solicited.

If any issues remain which may best be resolved through a telephone communication, the Examiner is requested to telephone the undersigned at the local Washington, D.C. telephone number listed below.

Date: December 18, 2002
JEL/DWW/att

Respectfully submitted,

James E. Ledbetter
Registration No. 28,732

Attorney Docket No. JEL 31015
STEVENS DAVIS, MILLER & MOSHER, L.L.P.
1615 L Street, N.W., Suite 850
P.O. Box 34387
Washington, D.C. 20043-4387
Telephone: (202) 408-5100
Facsimile: (202) 408-5200